Woojin Park

List of Publications by Year in Descending Order

48 papers	1,762 citations	21 h-index	41 g-index
53 ext. papers	1,937 ext. citations	5.3 avg, IF	4.14 L-index

#	Paper	IF	Citations
48	Low Power MoS2/Nb2O5 Memtransistor Device with Highly Reliable Heterosynaptic Plasticity. *Advanced Functional Materials*, **2021**, 31, 2104174	15.6	15
47	Unveiling the Role of Al2O3 Interlayer in Indium Gallium Zinc Oxide Transistors. *Physica Status Solidi (A) Applications and Materials Science*, **2021**, 218, 2000621	1.6	1
46	Al2O3-Induced Sub-Gap Doping on the IGZO Channel for the Detection of Infrared Light. *ACS Applied Electronic Materials*, **2020**, 2, 1478-1483	4	8
45	Novel Exfoliation of High-Quality 2H-MoS Nanoflakes for Solution-Processed Photodetector. *Nanomaterials*, **2020**, 10,	5.4	12
44	Enhanced Photoresponse of WS2 Photodetectors through Interfacial Defect Engineering Using a TiO2 Interlayer. *ACS Applied Electronic Materials*, **2020**, 2, 838-845	4	6
43	One-step HS reactive sputtering for 2D MoS/Si heterojunction photodetector. *Nanotechnology*, **2020**, 31, 225205	3.4	3
42	Modulation of Synaptic Plasticity Mimicked in Al Nanoparticle-Embedded IGZO Synaptic Transistor. *Advanced Electronic Materials*, **2020**, 6, 1901072	6.4	27
41	Artificial 2D van der Waals Synapse Devices via Interfacial Engineering for Neuromorphic Systems. *Nanomaterials*, **2020**, 10,	5.4	4
40	Improvement of the Bias Stress Stability in 2D MoS and WS Transistors with a TiO Interfacial Layer. *Nanomaterials*, **2019**, 9,	5.4	6
39	Facile fabrication of ZnO nanowire memory device based on chemically-treated surface defects. *Nanotechnology*, **2019**, 30, 155201	3.4	2
38	Highly Stable and Ultrafast Hydrogen Gas Sensor Based on 15 nm Nanogaps Switching in a Palladium Gold Nanoribbons Array. *Advanced Materials Interfaces*, **2019**, 6, 1801442	4.6	9
37	Contact Resistance Reduction of WS2 FETs Using High-Pressure Hydrogen Annealing. *IEEE Journal of the Electron Devices Society*, **2018**, 6, 164-168	2.3	17
36	Photonics: Enhanced Performance of MoS2 Photodetectors by Inserting an ALD-Processed TiO2 Interlayer (Small 5/2018). *Small*, **2018**, 14, 1870022	11	2
35	In-Line Tunnel Field Effect Transistor: Drive Current Improvement. *IEEE Journal of the Electron Devices Society*, **2018**, 6, 721-725	2.3	5
34	Enhanced Performance of MoS Photodetectors by Inserting an ALD-Processed TiO Interlayer. *Small* , **2018**, 14, 1703176	11	39
33	Contact resistance reduction of ZnO thin film transistors (TFTs) with saw-shaped electrode. *Nanotechnology*, **2018**, 29, 325202	3.4	3
32	Stable MoS2 Field-Effect Transistors Using TiO2 Interfacial Layer at Metal/MoS2 Contact. *Physica Status Solidi (A) Applications and Materials Science*, **2017**, 214, 1700534	1.6	10

31	Complementary Unipolar WS2 Field-Effect Transistors Using Fermi-Level Depinning Layers. *Advanced Electronic Materials*, **2016**, 2, 1500278	6.4	22
30	Reduction of low-frequency noise in multilayer MoS2 FETs using a Fermi-level depinning layer. *Physica Status Solidi - Rapid Research Letters*, **2016**, 10, 634-638	2.5	9
29	Patterned catalyst arrays of Pd/SnO2 core□shell nanowires for electrooxidations of biomass-derived alcohols. *Journal of Materials Chemistry A*, **2015**, 3, 13492-13499	13	13
28	Highly sensitive wide bandwidth photodetectors using chemical vapor deposited graphene. *Applied Physics Letters*, **2014**, 104, 161902	3.4	19
27	Characteristics of a pressure sensitive touch sensor using a piezoelectric PVDF-TrFE/MoS2 stack. *Nanotechnology*, **2013**, 24, 475501	3.4	34
26	Highly flexible and transparent multilayer MoS2 transistors with graphene electrodes. *Small*, **2013**, 9, 3295-300	11	154
25	Characteristics of light-induced electron transport from P3HT to ZnO-nanowire field-effect transistors. *Applied Physics Letters*, **2013**, 103, 223305	3.4	9
24	UV photoconductivity characteristics of ZnO nanowire field effect transistor treated by proton irradiation. *Thin Solid Films*, **2012**, 520, 3624-3628	2.2	4
23	Thermal stability of multilayer graphene films synthesized by chemical vapor deposition and stained by metallic impurities. *Nanotechnology*, **2012**, 23, 075702	3.4	45
22	Au nanoparticle-decorated graphene electrodes for GaN-based optoelectronic devices. *Applied Physics Letters*, **2012**, 101, 031115	3.4	42
21	Proton Irradiation-Induced Electrostatic Modulation in ZnO Nanowire Field-Effect Transistors With Bilayer Gate Dielectric. *IEEE Nanotechnology Magazine*, **2012**, 11, 918-923	2.6	3
20	The application of graphene as electrodes in electrical and optical devices. *Nanotechnology*, **2012**, 23, 112001	3.4	265
19	Investigation of threshold voltage instability induced by gate bias stress in ZnO nanowire field effect transistors. *Nanotechnology*, **2012**, 23, 485201	3.4	11
18	Characterization of ZnO Nanowire Field Effect Transistors by Fast Hydrogen Peroxide Solution Treatment. *Japanese Journal of Applied Physics*, **2012**, 51, 035001	1.4	1
17	Characterization on Improved Effective Mobility of Pentacene Organic Field-Effect Transistors Using Graphene Electrodes. *Japanese Journal of Applied Physics*, **2012**, 51, 02BK09	1.4	2
16	Characterization on Improved Effective Mobility of Pentacene Organic Field-Effect Transistors Using Graphene Electrodes. *Japanese Journal of Applied Physics*, **2012**, 51, 02BK09	1.4	2
15	Characterization of ZnO Nanowire Field Effect Transistors by Fast Hydrogen Peroxide Solution Treatment. *Japanese Journal of Applied Physics*, **2012**, 51, 035001	1.4	
14	Nonvolatile memory functionality of ZnO nanowire transistors controlled by mobile protons. *ACS Nano*, **2011**, 5, 558-64	16.7	38

13	Enhanced charge injection in pentacene field-effect transistors with graphene electrodes. *Advanced Materials*, **2011**, 23, 100-5	24	112
12	A study of graphene films synthesized on nickel substrates: existence and origin of small-base-area peaks. *Nanotechnology*, **2011**, 22, 045706	3.4	24
11	Enhanced characteristics of pentacene field-effect transistors with graphene electrodes and substrate treatments. *Applied Physics Letters*, **2011**, 99, 083306	3.4	23
10	Enhancement in the photodetection of ZnO nanowires by introducing surface-roughness-induced traps. *Nanotechnology*, **2011**, 22, 205204	3.4	46
9	Diameter-engineered SnO2 nanowires over contact-printed gold nanodots using size-controlled carbon nanopost array stamps. *ACS Nano*, **2010**, 4, 1829-36	16.7	45
8	Tuning of a graphene-electrode work function to enhance the efficiency of organic bulk heterojunction photovoltaic cells with an inverted structure. *Applied Physics Letters*, **2010**, 97, 213301	3.4	87
7	Tuning of the electronic characteristics of ZnO nanowire field effect transistors by proton irradiation. *ACS Nano*, **2010**, 4, 811-8	16.7	56
6	Large-scale patterned multi-layer graphene films as transparent conducting electrodes for GaN light-emitting diodes. *Nanotechnology*, **2010**, 21, 175201	3.4	233
5	Electrical properties of ZnO nanowire field effect transistors with varying high-k Al2O3 dielectric thickness. *Journal of Applied Physics*, **2010**, 107, 034504	2.5	24
4	Efficient bulk-heterojunction photovoltaic cells with transparent multi-layer graphene electrodes. *Organic Electronics*, **2010**, 11, 1864-1869	3.5	106
3	Logic inverters composed of controlled depletion-mode and enhancement-mode ZnO nanowire transistors. *Applied Physics Letters*, **2009**, 94, 173118	3.4	31
2	Tuning of operation mode of ZnO nanowire field effect transistors by solvent-driven surface treatment. *Nanotechnology*, **2009**, 20, 475702	3.4	19
1	Transient drain current characteristics of ZnO nanowire field effect transistors. *Applied Physics Letters*, **2009**, 95, 123101	3.4	21